

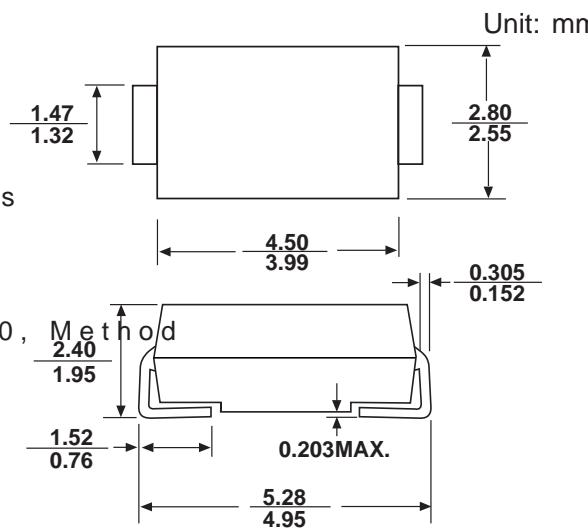
## 60\$ PLASTIC SILICON RECTIFIERS

## FEATURES

- "For surface mounted applications
- "Low profile package
- "Glass Passivated Chip Junction
- "Easy to pick and place
- "High efficiency
- "Lead free in comply with EU Directives

## MECHANICAL DATA

- "Case: SMA
- "Terminals: Solderable per MIL-STD-750, Method 2.40
- "Approx. Weight: 0.055 g / 0.002 oz



## MAXIMUM RATINGS AND CHARACTERISTICS

# f &amp; P E L H Q T W S H U D X Q O R H W K H U Z R W H G

Parameter	Symbol	sUS1A	US1B	US1D	US1G	US1J	US1K	US1M	Units
Maximum Repetitive Peak Reverse Voltage	VR <sub>Repet</sub>	50	100	200	400	600	800	1000	V
Maximum RMS voltage	VR <sub>RMS</sub>	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	VD <sub>C</sub>	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at $T_c = 12^\circ\text{C}$	CF <sub>(AV)</sub>				1				A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load	IF <sub>SM</sub>				30				A
Maximum Instantaneous Forward Voltage at 1 A	V <sub>F</sub>	1.0			1.3		1.65		V
Maximum DC Reverse Current at $T_a = 2^\circ\text{C}$ at Rated DC Blocking Voltage $T_a = 2^\circ\text{C}$	IR				5		100		mA
Maximum Reverse Recovery Time	trr			50			75		ns
Typical Thermal Resistance	$R_{JA}$				75				$^\circ\text{C}/\text{W}$
Typical Junction Capacitance	C <sub>j</sub>				15				pF
Operating and Storage Temperature Range	T <sub>Operating</sub> to T <sub>Storage</sub>			-55 ~ +150					$^\circ\text{C}$

Measured with  $I = 0.15 \text{ mA}$   $A_r = 0.25 \text{ A}$ 

P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.

Measured at 1 MHz and applied reverse voltage of 4 V D.C.

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## RATINGS AND CHARACTERISTIC CURVES